ŧ

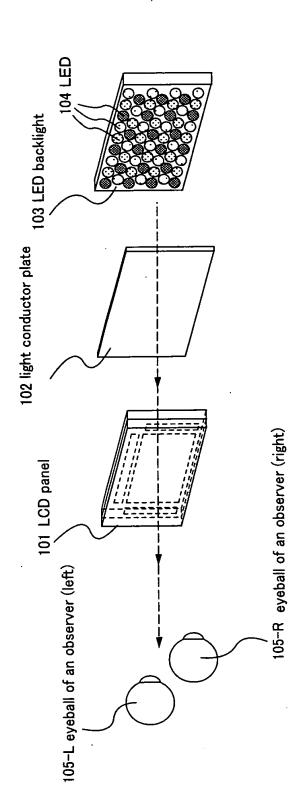


Fig.

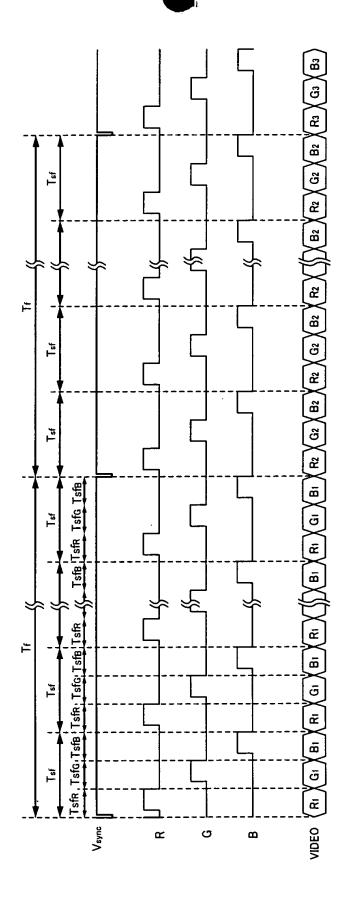


Fig. 2

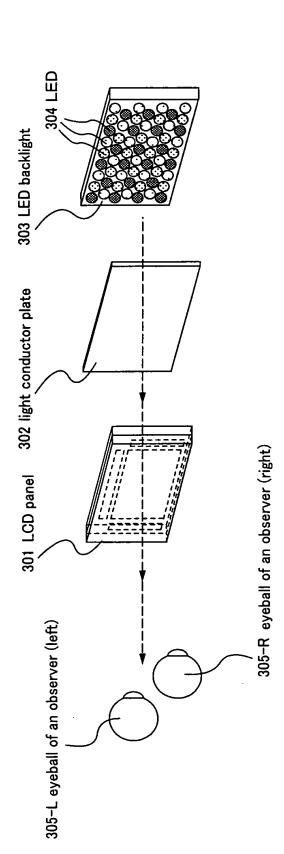


Fig.

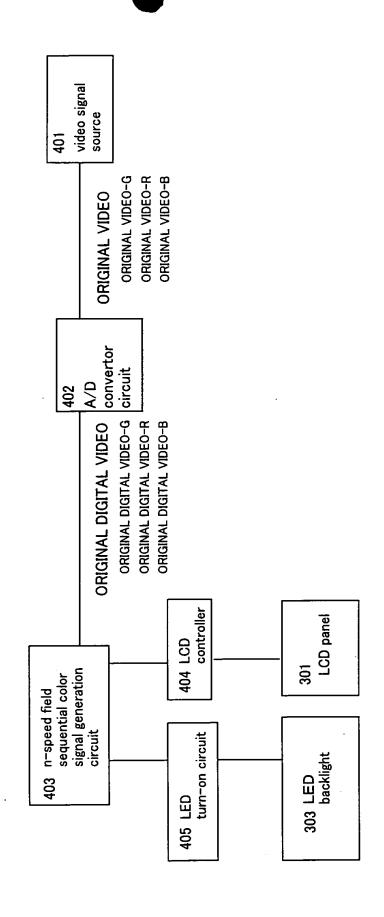


Fig.

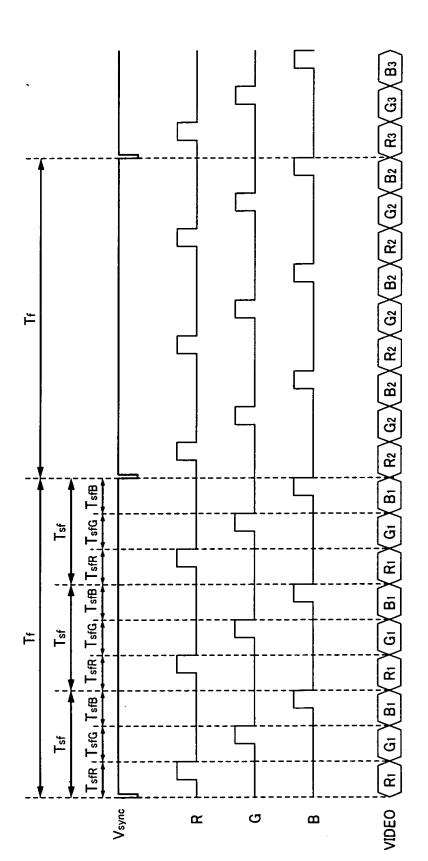


Fig. 5

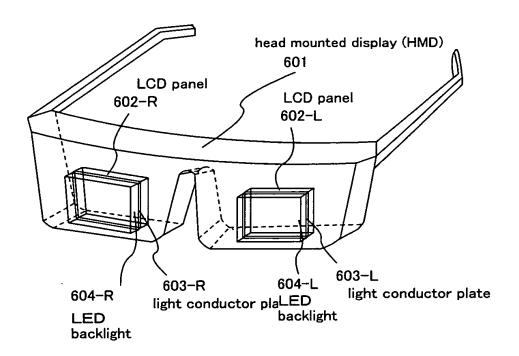
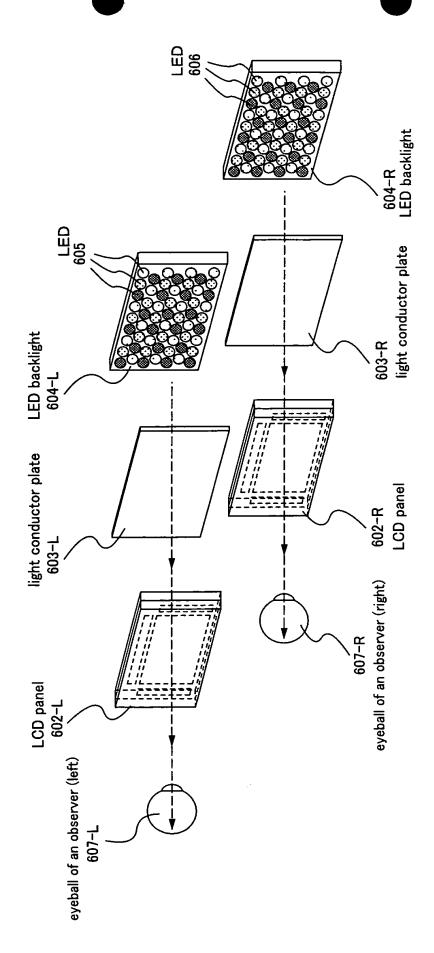


Fig. 6



Fig

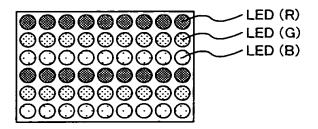


Fig. 8(A)

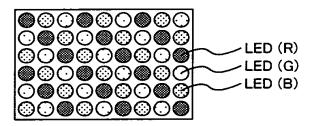


Fig. 8(B)

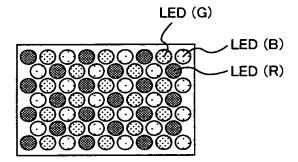


Fig. 8(C)

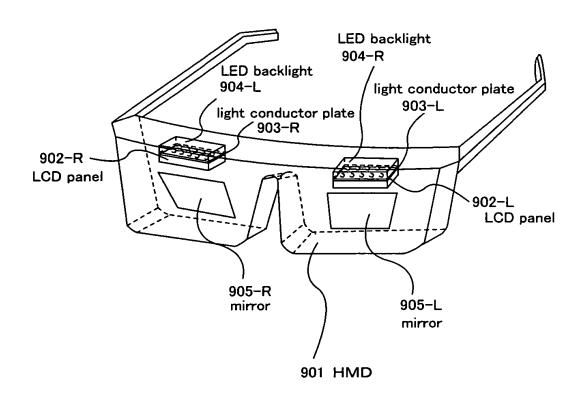


Fig. 9

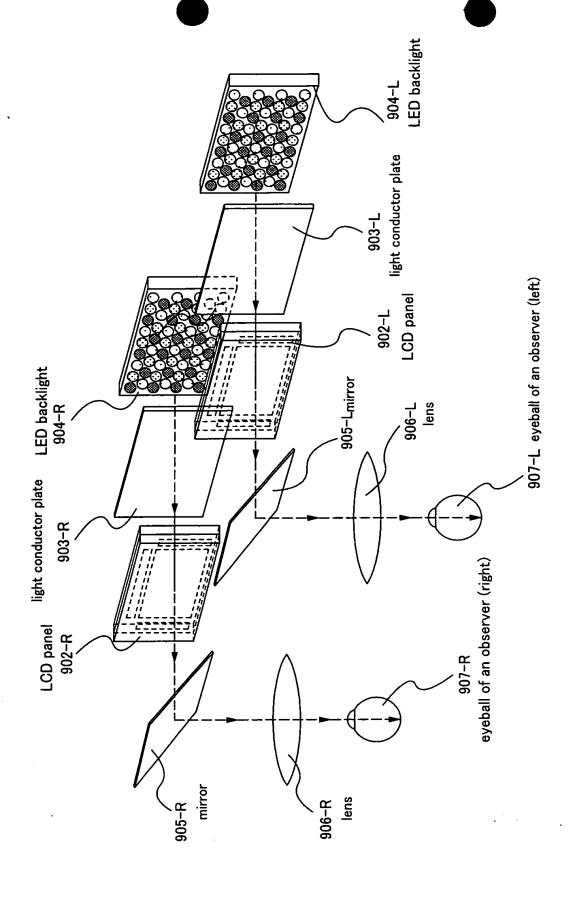


Fig. 10

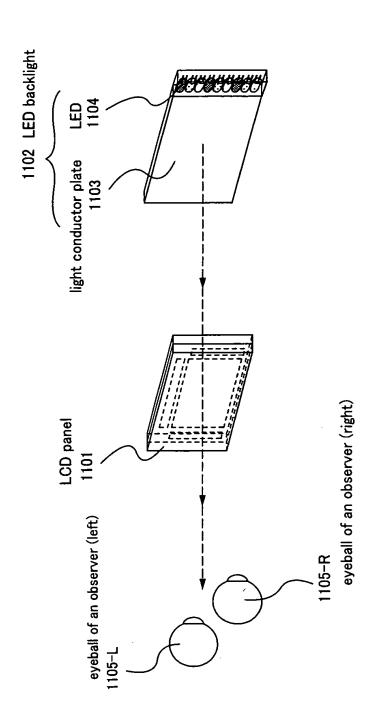


Fig. 1

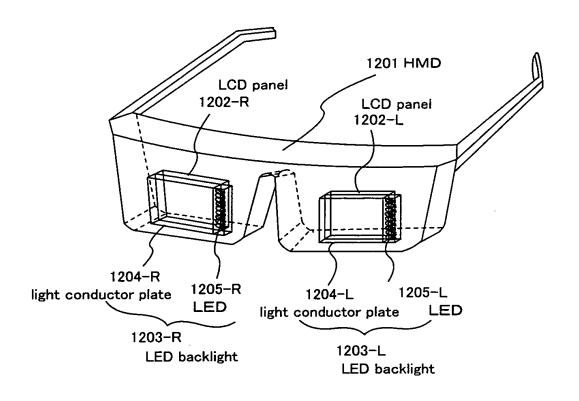


Fig. 12

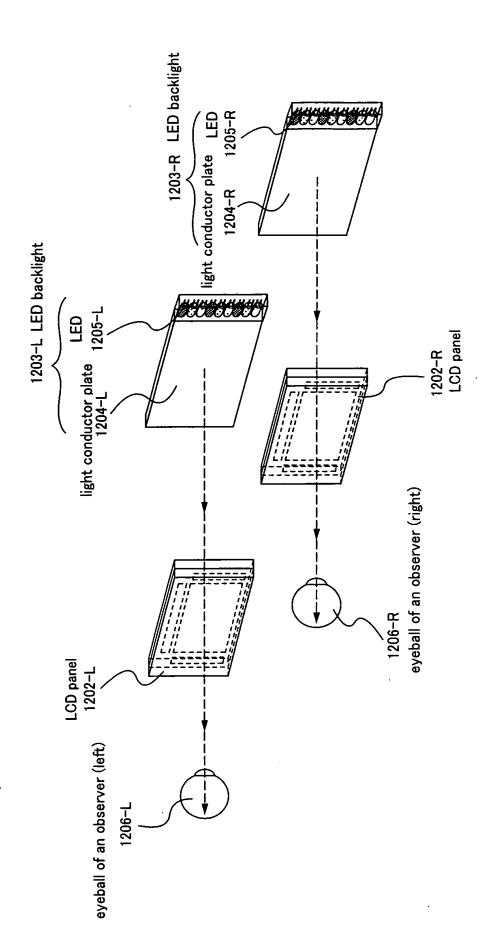
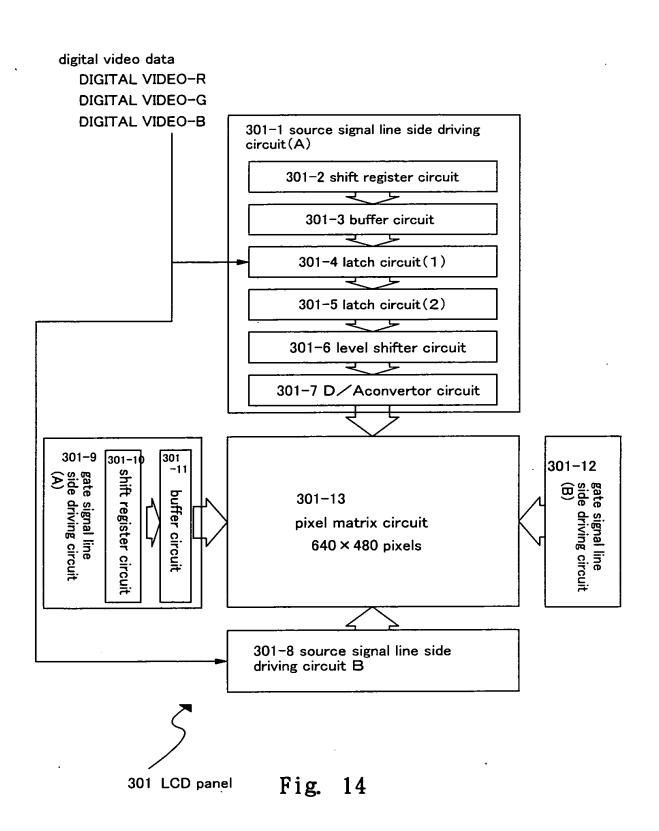


Fig. 18



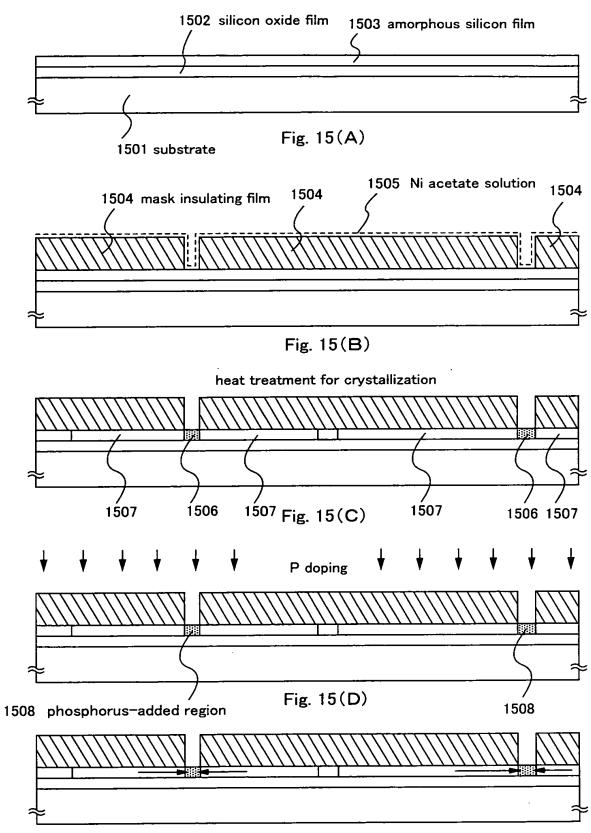


Fig.15(E)

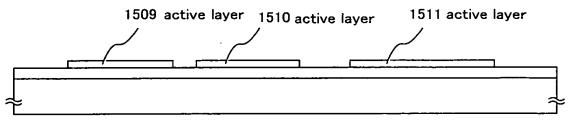


Fig. 16(A)

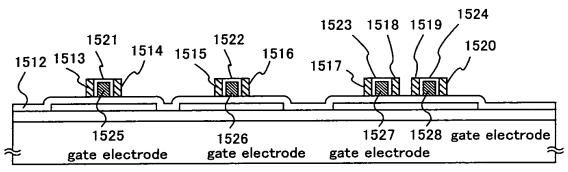


Fig. 16(B)

1513~1520 : porous anodic oxide films 1521~1524 : non-porous anodic oxide films

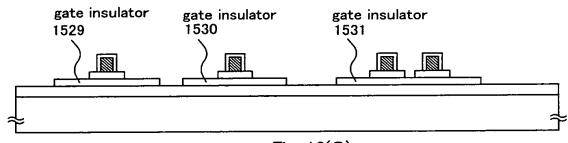
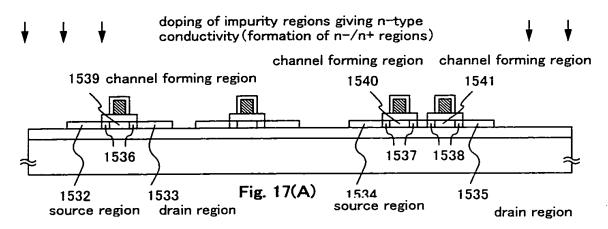


Fig. 16(C)



1536, 1537, 1538: low concentration impurity region

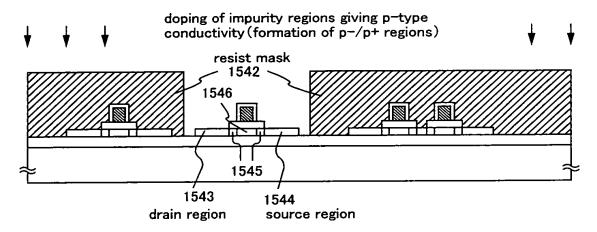


Fig. 17(B) 1545 : low concentration impurity region

1546 : channel forming region

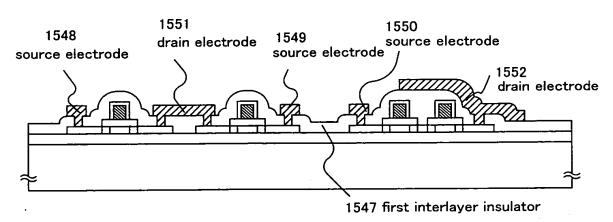


Fig. 17(C)

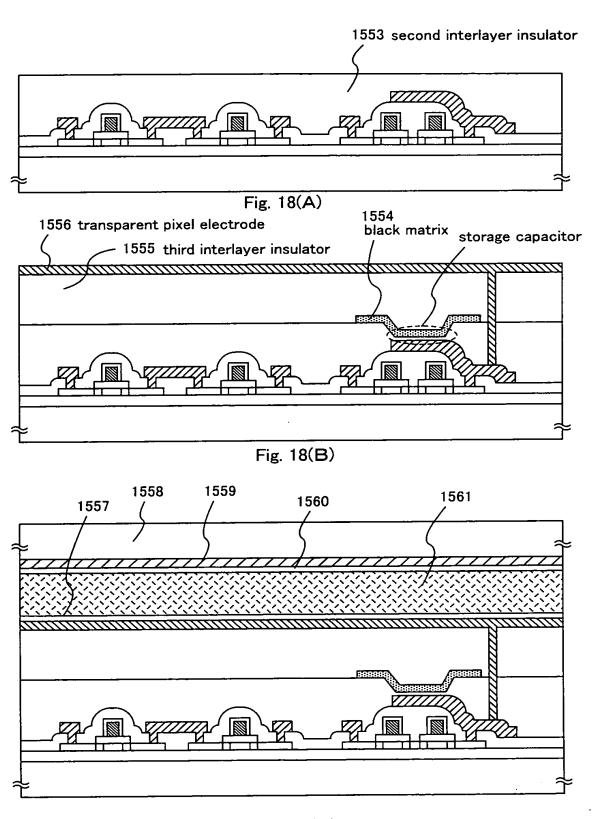
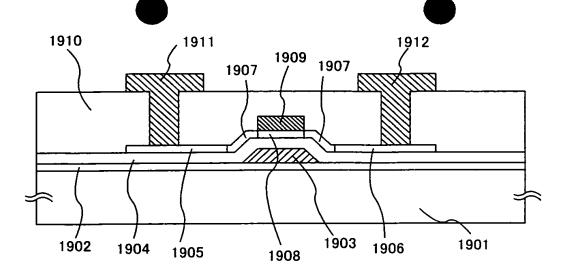


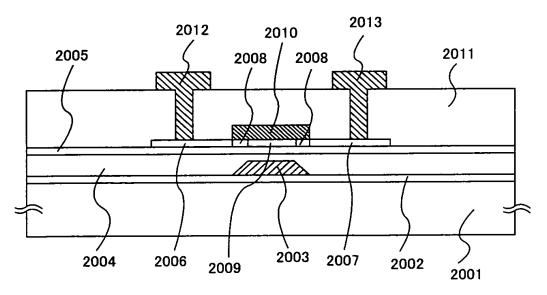
Fig. 18(C)



1901 substrate 1907 LDD

1902 silicon oxide film 1908 channel forming region
1903 gate electrode 1909 channel protecting film
1904 gate insulating film 1910 interlayer insulator
1905 source region 1911 source electrode
1906 drain region 1912 drain electrode

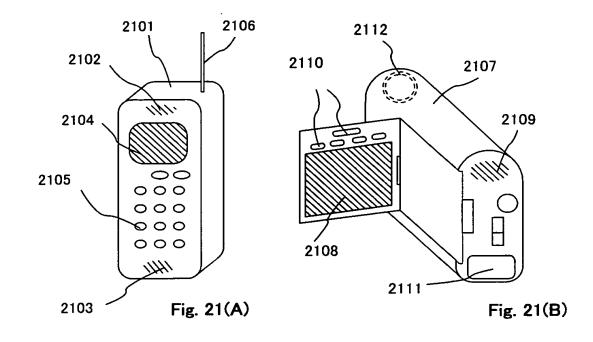
Fig. 19



2001 substrate 2008 (LDD)

2002 silicon oxide film 2009 channel forming region
2003 gate electrode 2010 channel protecting film
2004 benzocyclobutene(BCB)2011 interlayer insulator
2005 silicon nitride 2012 source electrode
2006 source region 2013 drain electrode
2007 drain region

Fig. 20



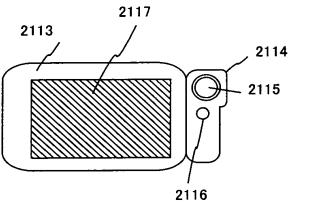


Fig. 21(C)

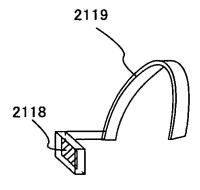


Fig. 21(D)

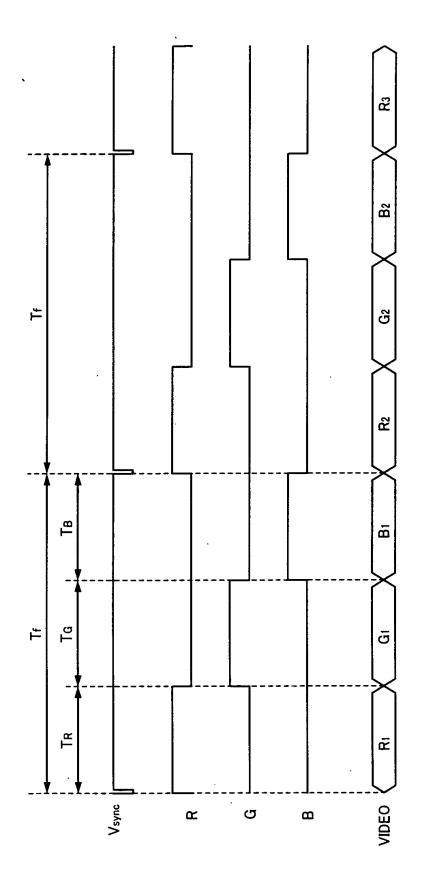


Fig. 22 Prior Art

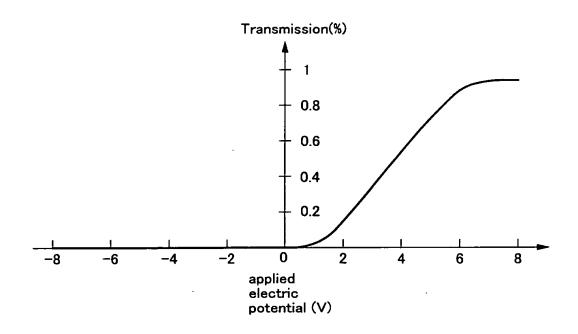


Fig. 23(A)

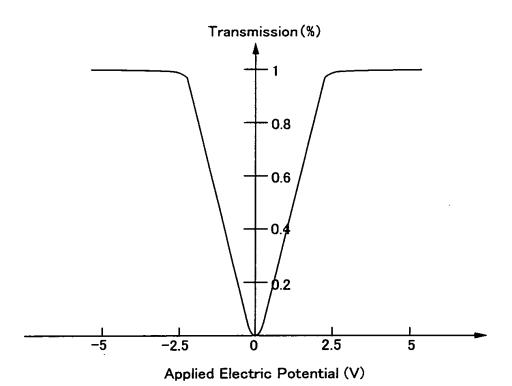
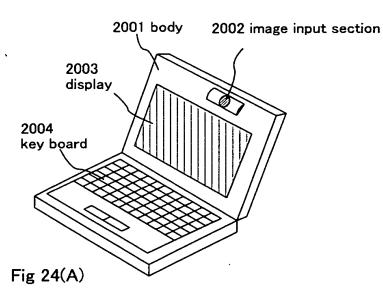


Fig. 23(B)



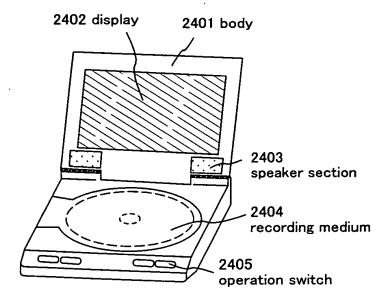


Fig. 24(C)

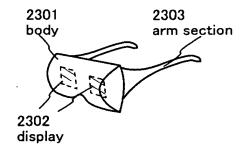


Fig. 24(B)

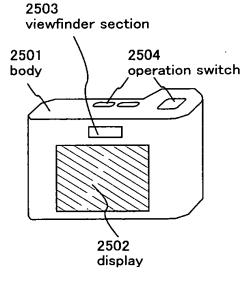


Fig. 24(D)